

DESCRIPTION

The MMBR911LT1 is a low noise, high gain, discrete silicon bipolar transistors housed in low cost plastic packages.

IMPORTANT: For the most current data, consult MICROSEMI's website: <http://www.microsemi.com>

KEY FEATURES

- ✎ High FTau-6.0 GHz
- ✎ Low noise-2.9dB@1GHz
- ✎ Low cost SOT23 package

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25 C)

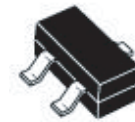
Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	20	V
V _{CEO}	Collector-Emitter Voltage	12	V
V _{EBO}	Emitter-Base Voltage	2.0	V
I _C	Device Current	60	mA
P _{DISS}	Power Dissipation	333	mW
T _J	Junction Temperature	150	C
T _{STG}	Storage Temperature	-55 to +150	C

THERMAL DATA

R _{TH(j-c)}	Junction-Case Thermal Resistance	225	C/W
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APPLICATIONS/BENEFITS

- ✎ LNA, Oscillator, Pre-Driver



SOT-23
MMBR911LT1

STATIC ELECTRICAL SPECIFICATIONS (T_{case} = 25 C)

Symbol	Test Conditions	Min.	Typ.	Max.	Units
BV _{CBO}	I _C = .1mA I _E = 0	20			V
BV _{CEO}	I _C = 1.0mA I _B = 0	12			V
I _{CBO}	V _{CB} = 15V I _E = 0			50	nA
h _{FE}	V _{CE} = 10V I _C = 30mA	30		200	

DYNAMIC ELECTRICAL SPECIFICATIONS (T_{case} = 25 C)

Symbol	Test Conditions	Min.	Typ.	Max.	Units
C _{CB}	V _{CB} = 10 V f = 1.0 MHz		1.0		pF
FTau	V _{CE} = 10 V I _C = 30 mA f = 1.0 GHz		6.0		GHz
NFmin	V _{CE} = 10 V I _C = 10 mA f = 1.0 GHz		2.9		dB
GNF	V _{CE} = 10 V I _C = 10 mA f = 1.0 GHz		11		dB